

isc Silicon PNP Darlington Power Transistor

2N6287

DESCRIPTION

- Built-in Base-Emitter Shunt Resistors
- High DC current gain-
 $h_{FE} = 750$ (Min) @ $I_C = -10$ Adc
- Collector-Emitter Sustaining Voltage-
 $V_{CEO(SUS)} = -100V$ (Min)
- Complement to type 2N6284
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

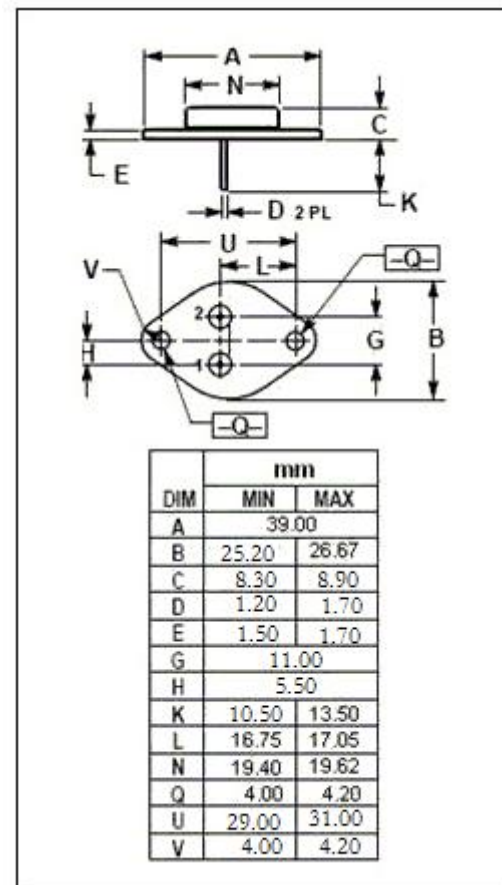
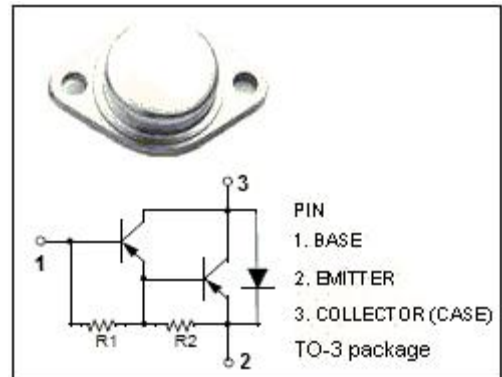
- Intended for general purpose amplifier and low frequency switching applications, such as linear and switching industrial equipment.

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current -Continuous	-20	A
I_{CP}	Collector Current-Peak	-40	A
I_B	Base Current	-0.5	A
P_C	Collector Power Dissipation@ $T_C=25^{\circ}C$	160	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-65~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	ThermalResistance, Junction to Case	1.09	$^{\circ}C/W$



isc Silicon PNP Darlington Power Transistor**2N6287****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -50mA ; I _B = 0	-100		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = -10A; I _B = -40mA		-2.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = -20A; I _B = -200mA		-3.0	V
V _{BE(sat)}	Base-Emitter Saturation voltage	I _C = -20A; I _B = -200mA		-4.0	V
V _{BE(on)}	Base-Emitter On voltage	I _C = -10A; V _{CE} = -3V		-2.8	V
I _{CEO}	Collector Cutoff current	V _{CE} = -50V; I _B =0		-1.0	mA
I _{CEX}	Collector Cutoff current	V _{CE} = -100V; V _{BE(off)} = -1.5V V _{CE} = -100V; V _{BE(off)} = -1.5V, T _C =150°C		-0.5 -5.0	mA
I _{EBO}	Emitter Cut-off current	V _{EB} = -5V; I _C = 0		-2.0	mA
h _{FE-1}	DC Current Gain	I _C = -10A; V _{CE} = -3V	750	18000	
h _{FE-2}	DC Current Gain	I _C = -20A; V _{CE} = -3V	100		
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1.0MHz		600	pF

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